



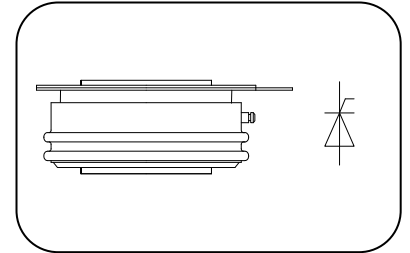
Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$ **1800A**
 V_{DRM}/V_{RRM} **2400~3000V**
 t_q **30~60μs**
 I_{TSM} **21 kA**
 I^2t **2205 10³A²S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, T _c =55°C	125		1800	1920	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM} & V_{RRM}$, t _p =10ms $V_{DSM} & V_{RSM} = V_{DRM} & V_{RRM} + 100V$	125	2400		3000	V
I_{DRM} I_{RRM}	Repetitive peak current	$V_D = V_{DRM}$ $V_R = V_{RRM}$	125			140	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			21	kA
I^2t	I ² T for fusing coordination					2205	A ² s*10 ³
V_{TO}	Threshold voltage		125			1.48	V
r_T	On-state slop resistance					0.28	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=4000A, F=32kN$	25			3.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$, $I_{TM}=(2-3)I_{T(AV)}$, t=5s, Gate pulse t _r ≤0.5μs I _{GM} =1.5A f=50Hz	125			600	A/μs
Q _{rr}	Recovery charge	$I_{TM}=1800A, t_p=1000μs$, di/dt=-20A/μs, V _R =100V	125		860		μC
t _q	Circuit commutated turn-off time	$I_{TM}=1800A, t_p=1000μs, V_R=100V$ dv/dt=30V/μs, di/dt=-20A/μs	125	30		60	μs
I _{GT}	Gate trigger current	$V_A=12V, I_A=1A$	25	40		250	mA
V _{GT}	Gate trigger voltage			0.9		2.5	V
I _H	Holding current			20		400	mA
V _{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
R _{th(j-c)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 32kN				0.013	°C /W
R _{th(c-h)}	Thermal resistance case to heat sink					0.0035	
F _m	Mounting force			27		36	kN
T _{stg}	Stored temperature			-40		140	°C
W _t	Weight				820/1080		g
Outline	KT70cT/dT						

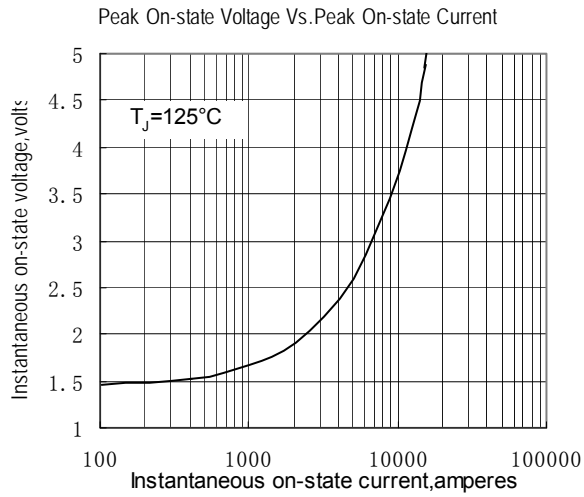


Fig.1

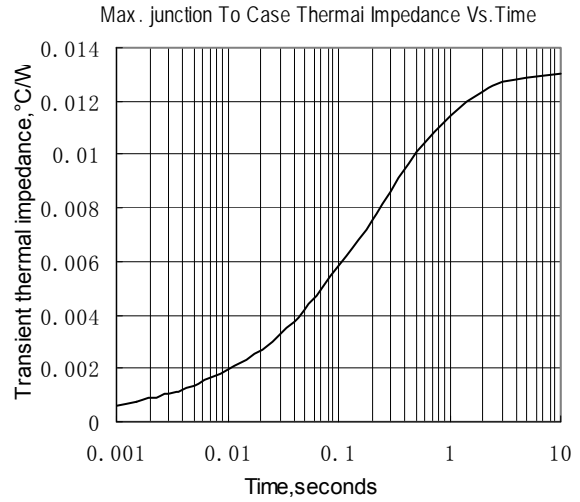


Fig.2

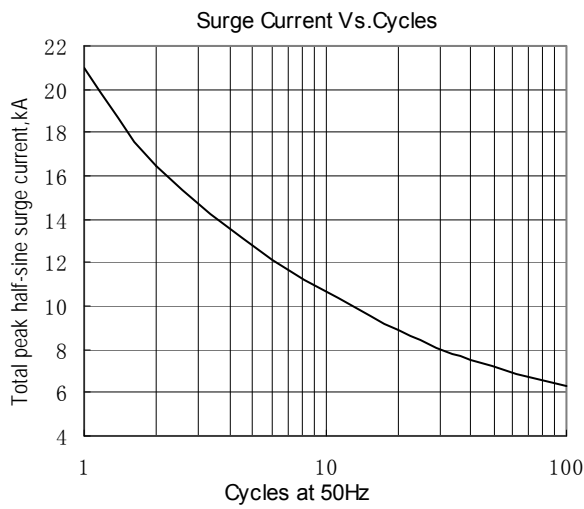


Fig.3

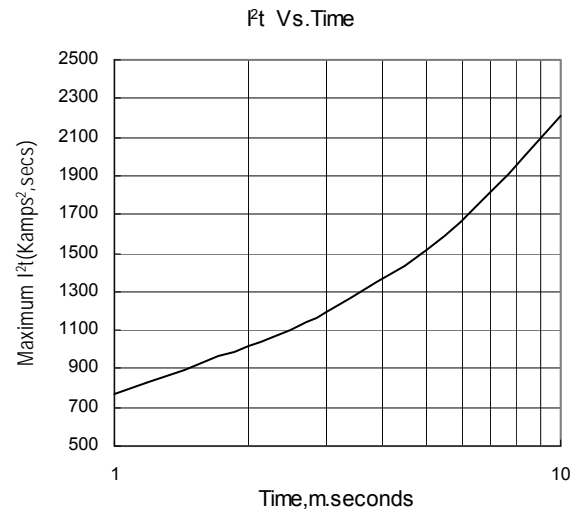


Fig.4

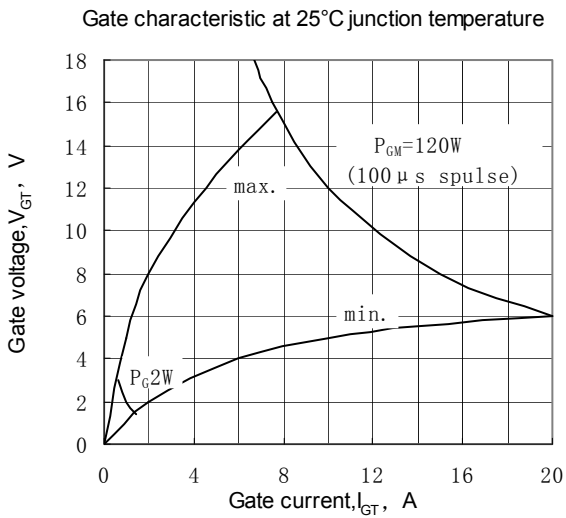


Fig.5

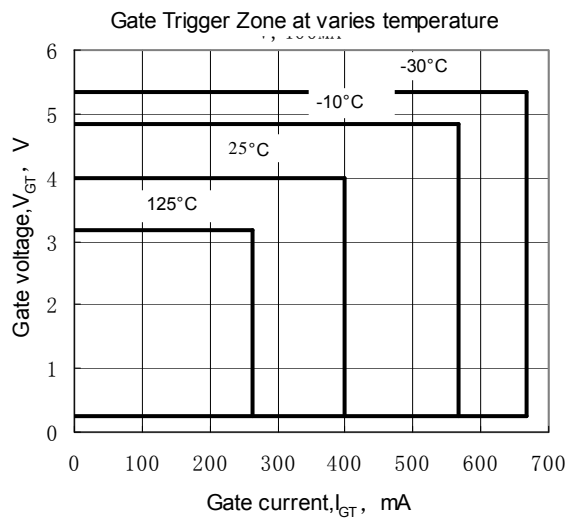


Fig.6



Outline:

图12-KT70cT

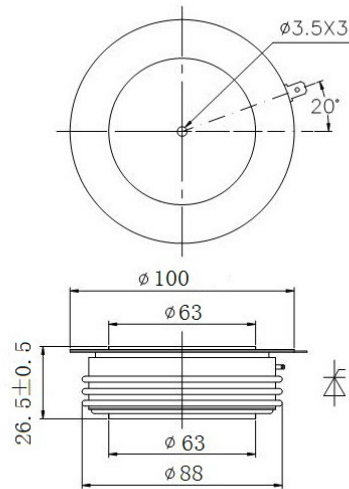
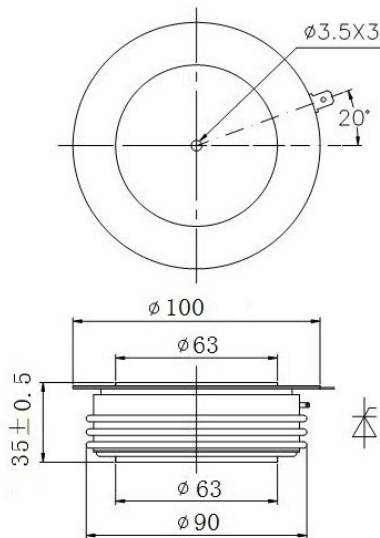


图13-KT70dT



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